PGPUB Interference

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	(laser with mark$4 with (spray$4 adhesive resin viscosity) with (semiconductor silicon die wafer)).clm.	US-PGPUB	OR	ON	2006/09/27 10:30
L2	3	1 and filler	US-PGPUB	OR	ON	2006/09/27 10:01
L3	3	1 and (filler with color$4)	US-PGPUB	OR	ON	2006/09/27 10:03
L4	2	1 and (filler with color$4) and visco$9	US-PGPUB	OR	ON	2006/09/27 10:03
L5	212	(laser with mark$4 near5 (semiconductor die wafer)).clm.	US-PGPUB; USPAT	OR	ON	2006/09/27 10:33
L6	91	"438"/$.ccls. and (laser with mark$4 near5 (semiconductor die wafer)).clm.	US-PGPUB; USPAT	OR	ON	2006/09/27 10:34
L7	20	"438"/$.ccor. and (laser with marking near5 (semiconductor die wafer)).clm.	US-PGPUB; USPAT	OR	ON	2006/09/27 10:55
L8	2	6 and color$4.clm.	US-PGPUB; USPAT	OR	ON	2006/09/27 10:55

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S28	1	("6432796").PN.	USPAT; USOCR	OR	OFF	2006/09/26 11:08
S37	2	(("4344006") or ("5641997")).PN.	USPAT; USOCR	OR	OFF	2006/09/26 11:35
S39	1	S37 and spray$5 with visco$9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:18
S40	6196581	b0$9 b1$9 b2$9 b3$9 b4$9 b5$9 b6$9 b7$9 b8$9 b9$9 f0$9 f1$9 f2$9 f3$9 f4$9 f5$9 f6$9 f7$9 f8$9 f9$9 g0$9 g1$9 g2$9 g3$9 g4$9 g5$9 g6$9 g7$9 g8$9 g9$9 h0$9 h1$9 h2$9 h3$9 h4$9 h5$9 h6$9 h7$9 h8$9 h9$9	JPO	OR	ON	2006/09/26 11:22
S41	13	S40 and (semiconduct$4 silicon die wafer) and mark$3 and laser and (spray$4 sputter$4)	JPO	OR	ON	2006/09/26 11:29
S42	21	S40 and (semiconduct$4 silicon die wafer) and mark$3 and laser and adhesiv$5	JPO	OR	ON	2006/09/26 11:30
S43	44	S40 and (semiconduct$4 silicon die wafer) and laser and ((burn$4 cut$4 mark$3) with adhesiv$5)	JPO	OR	ON	2006/09/26 11:31
S44	3	(("4344006") or ("5641997") or ("6177093")).PN.	USPAT; USOCR	OR	OFF	2006/09/26 11:37
S45	1	S44 and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:37
S46	1	S44 and laser with mark$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:38
S47	0	S44 and (laser with mark$4) same (spray$4 adhesiv$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:47
S48	1	S44 and (laser with mark$4) and (spray$4 adhesiv$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:45

EAST Search History

S49	0	S44 and (laser with mark$4) and (inactiv$4 with surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:46
S50	0	S44 and laser and mark$4 and inactiv$4 and surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:46
S51	0	S44 and laser and mark$4 and inactiv$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:46
S52	1	S44 and laser and mark$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:46
S53	3	S40 and (laser with mark$4) and (spray$4 with adhesiv$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:51
S54	0	S40 and (laser with mark$4) and (spray$4 with adhesiv$5) and (semiconduct$4 silicon wafer die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:51
S55	4	S40 and (laser with mark$4 with adhesiv$5) and (semiconduct$4 silicon wafer die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 11:53
S56	18	S40 and (laser with (mark$4 burn$4 cut$4) with adhesiv$5) and (semiconduct$4 silicon wafer die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 12:00
S57	160	S40 and (laser with (mark$4 burn$4 cut$4) with (adhesiv$5 resin$3)) and (semiconduct$4 silicon wafer die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 12:02
S58	85	S40 and (laser with (mark$4 burn$4 cut$4) near5 (adhesiv$5 resin$3)) and (semiconduct$4 silicon wafer die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 12:45

EAST Search History

S59	2	S40 and (laser with (mark$4 burn$4 cut$4) near5 (adhesiv$5 resin$3)) and (semiconduct$4 silicon wafer die) and ((spray$4 sputter$4) with (adhesiv$5 resin$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 12:06
S60	2	S40 and (laser with (mark$4 burn$4 cut$4) with (adhesiv$5 resin$3)) and (semiconduct$4 silicon wafer die) and ((spray$4 sputter$4) with (adhesiv$5 resin$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 12:12
S61	49	S40 and (laser with (mark$4 burn$4) near5 (adhesiv$5 resin$3)) and (semiconduct$4 silicon wafer die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/26 12:45
S62	6196581	b0$9 b1$9 b2$9 b3$9 b4$9 b5$9 b6$9 b7$9 b8$9 b9$9 f0$9 f1$9 f2$9 f3$9 f4$9 f5$9 f6$9 f7$9 f8$9 f9$9 g0$9 g1$9 g2$9 g3$9 g4$9 g5$9 g6$9 g7$9 g8$9 g9$9 h0$9 h1$9 h2$9 h3$9 h4$9 h5$9 h6$9 h7$9 h8$9 h9$9	JPO	OR	ON	2006/09/27 08:46
S63	45	S62 and (laser with mark$4 near5 (adhesiv$5 resin$3)) and (semiconduct$4 silicon wafer die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 08:48
S64	3	S62 and (laser with mark$4 near5 (adhesiv$5 resin$3)) and (semiconduct$4 silicon wafer die) and ((back backside inactive nonactive opposite) with mark$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 08:49